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NTMFD4C87N

PowerPhase, Dual N-Channel SO8FL 30 V, High Side 20 A / Low Side 26 A

Features

- Co-Packaged Power Stage Solution to Minimize Board Space
- Minimized Parasitic Inductances
- Optimized Devices to Reduce Power Losses
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- DC-DC Converters
- System Voltage Rails
- Point of Load

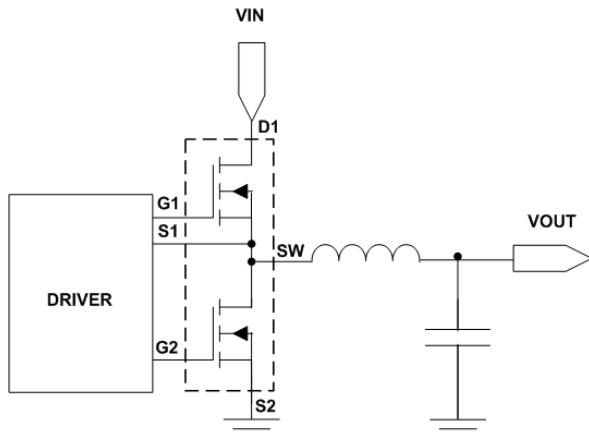


Figure 1. Typical Application Circuit

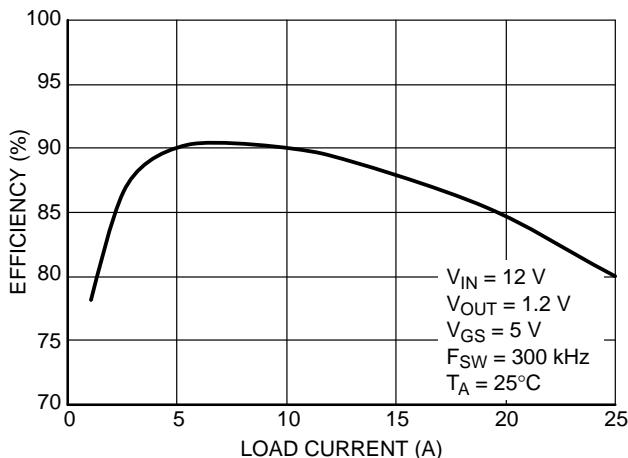


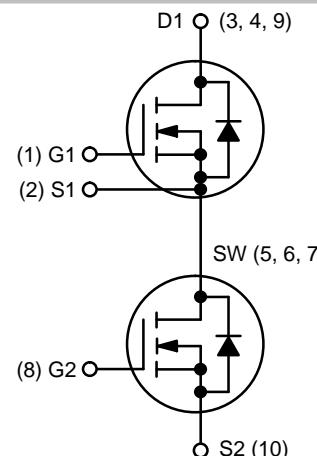
Figure 2. Typical Efficiency Performance
POWERPHASEGEVB Evaluation Board



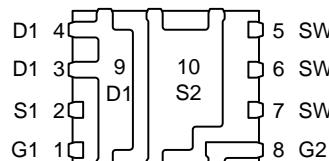
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$V_{(BR)DSS}$	$R_{DS(ON)\text{ MAX}}$	$I_D \text{ MAX}$
Q1 Top FET 30 V	5.4 m Ω @ 10 V	20 A
	8.1 m Ω @ 4.5 V	
Q2 Bottom FET 30 V	3.1 m Ω @ 10 V	26 A
	4.3 m Ω @ 4.5 V	



PIN CONNECTIONS



(Bottom View)

MARKING DIAGRAM



4C87N = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering and shipping information on page 10 of this data sheet.

NTMFD4C87N

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Value	Unit				
Drain-to-Source Voltage	V _{DSS}	30	V				
Drain-to-Source Voltage							
Gate-to-Source Voltage	V _{GS}	±20	V				
Gate-to-Source Voltage							
Continuous Drain Current R _{θJA} (Note 1)	Steady State	T _A = 25°C T _A = 85°C	Q1	I _D	15.4	A	
		T _A = 25°C T _A = 85°C			11.1		
		T _A = 25°C	Q2		19.5		
		T _A = 85°C			14.1		
Power Dissipation R _{θJA} (Note 1)		T _A = 25°C	Q1 Q2	P _D	1.89	W	
		T _A = 85°C					
Continuous Drain Current R _{θJA} ≤ 10 s (Note 1)		T _A = 25°C T _A = 85°C	Q1	I _D	21.0	A	
		T _A = 25°C T _A = 85°C			15.1		
Power Dissipation R _{θJA} ≤ 10 s (Note 1)		T _A = 25°C	Q2		26.6		
		T _A = 85°C			19.2		
Continuous Drain Current R _{θJA} (Note 2)		T _A = 25°C	Q1 Q2	P _D	3.51	W	
		T _A = 85°C					
Power Dissipation R _{θJA} (Note 2)		T _A = 25 °C	Q1 Q2	I _D	11.7	A	
		T _A = 85°C			8.5		
Pulsed Drain Current		T _A = 25°C t _p = 10 μs	Q1 Q2		14.9		
		T _A = 85°C			10.7		
Operating Junction and Storage Temperature		T _A = 25 °C	Q1 Q2	I _{DM}	1.10	W	
		t _p = 10 μs			160		
Source Current (Body Diode)		T _A = 25 °C	Q1 Q2	T _J , T _{STG}	260	A	
		t _p = 10 μs			-55 to +150		
Drain to Source DV/DT				dV/dt	6	V/ns	
Single Pulse Drain-to-Source Avalanche Energy (T _J = 25C, V _{DD} = 50 V, V _{GS} = 10 V, L = 0.1 mH, R _G = 25 Ω)	I _L = 20 A _{pk} I _L = 30 A _{pk}	Q1 Q2	EAS	20 45		mJ	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260		°C	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu.
2. Surface-mounted on FR4 board using the minimum recommended pad size of 100 mm².

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THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Ambient – Steady State (Note 3)	$R_{\theta JA}$	66.0	$^{\circ}\text{C}/\text{W}$
Junction-to-Ambient – Steady State (Note 4)	$R_{\theta JA}$	113.7	
Junction-to-Ambient – ($t \leq 10 \text{ s}$) (Note 3)	$R_{\theta JA}$	35.6	

3. Surface-mounted on FR4 board using 1 sq-in pad, 2 oz Cu.
 4. Surface-mounted on FR4 board using the minimum recommended pad size of 100 mm².

ELECTRICAL CHARACTERISTICS ($T_J = 25^{\circ}\text{C}$ unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Break-down Voltage	Q1	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V
	Q2			30			
Drain-to-Source Break-down Voltage Temperature Coefficient	Q1	$V_{(\text{BR})\text{DSS}} / T_J$			15.8		$\text{mV} / ^{\circ}\text{C}$
	Q2				15.3		
Zero Gate Voltage Drain Current	Q1	I_{DSS}	$V_{\text{GS}} = 0 \text{ V}, V_{\text{DS}} = 24 \text{ V}$	$T_J = 25^{\circ}\text{C}$		1	μA
				$T_J = 125^{\circ}\text{C}$		10	
	Q2		$V_{\text{GS}} = 0 \text{ V}, V_{\text{DS}} = 24 \text{ V}$	$T_J = 25^{\circ}\text{C}$		1	
Gate-to-Source Leakage Current	Q1	I_{GSS}	$V_{\text{GS}} = 0 \text{ V}, V_{\text{DS}} = +20 \text{ V}$			100	nA
	Q2					100	

ON CHARACTERISTICS (Note 5)

Gate Threshold Voltage	Q1	$V_{\text{GS}(\text{TH})}$	$V_{\text{GS}} = V_{\text{DS}}, I_D = 250 \mu\text{A}$	1.3		2.2	V
	Q2			1.3		2.2	
Negative Threshold Temperature Coefficient	Q1	$V_{\text{GS}(\text{TH})} / T_J$			5.0		$\text{mV} / ^{\circ}\text{C}$
	Q2				5.1		
Drain-to-Source On Resistance	Q1	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 10 \text{ V}$	$I_D = 30 \text{ A}$		4.3	$\text{m}\Omega$
			$V_{\text{GS}} = 4.5 \text{ V}$	$I_D = 18 \text{ A}$		6.5	
	Q2		$V_{\text{GS}} = 10 \text{ V}$	$I_D = 30 \text{ A}$		2.5	
			$V_{\text{GS}} = 4.5 \text{ V}$	$I_D = 30 \text{ A}$		3.4	

CAPACITANCES

Input Capacitance	Q1	C_{ISS}	$V_{\text{GS}} = 0 \text{ V}, f = 1 \text{ MHz}, V_{\text{DS}} = 15 \text{ V}$		1252		pF	
	Q2				1939			
Output Capacitance	Q1	C_{OSS}			610			
	Q2				1055			
Reverse Capacitance	Q1	C_{RSS}			129			
	Q2				49			

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
 6. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit	
CHARGES, CAPACITANCES & GATE RESISTANCE								
Total Gate Charge	Q1	$Q_{G(\text{TOT})}$	$V_{GS} = 4.5 \text{ V}, V_{DS} = 15 \text{ V}; I_D = 30 \text{ A}$		10.9		nC	
	Q2				13.8			
Threshold Gate Charge	Q1	$Q_{G(\text{TH})}$			1.2			
	Q2				2.0			
Gate-to-Source Charge	Q1	Q_{GS}			3.4			
	Q2				5.5			
Gate-to-Drain Charge	Q1	Q_{GD}			5.4			
	Q2				3.6			
Total Gate Charge	Q1	$Q_{G(\text{TOT})}$	$V_{GS} = 10 \text{ V}, V_{DS} = 15 \text{ V}; I_D = 30 \text{ A}$		22.2		nC	
	Q2				30.3			
Gate Resistance	Q1	R_G	$T_A = 25^\circ\text{C}$		1.0		Ω	
	Q2				1.0			

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	Q1	$t_{d(\text{ON})}$	$V_{GS} = 4.5 \text{ V}, V_{DS} = 15 \text{ V}, I_D = 15 \text{ A}, R_G = 3.0 \Omega$		8.9		ns	
	Q2				10.6			
Rise Time	Q1	t_r			21.2			
	Q2				4.6			
Turn-Off Delay Time	Q1	$t_{d(\text{OFF})}$			15.3			
	Q2				21			
Fall Time	Q1	t_f			4.4			
	Q2				4.9			

SWITCHING CHARACTERISTICS (Note 6)

Turn-On Delay Time	Q1	$t_{d(\text{ON})}$	$V_{GS} = 10 \text{ V}, V_{DS} = 15 \text{ V}, I_D = 15 \text{ A}, R_G = 3.0 \Omega$		6.7		ns	
	Q2				8.1			
Rise Time	Q1	t_r			19.5			
	Q2				15			
Turn-Off Delay Time	Q1	$t_{d(\text{OFF})}$			20.1			
	Q2				26.2			
Fall Time	Q1	t_f			2.8			
	Q2				3.1			

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Voltage	Q1	V_{SD}	$V_{GS} = 0 \text{ V}, I_S = 10 \text{ A}$	$T_J = 25^\circ\text{C}$		0.82		V	
				$T_J = 125^\circ\text{C}$		1.15			
	Q2		$V_{GS} = 0 \text{ V}, I_S = 10 \text{ A}$	$T_J = 25^\circ\text{C}$		0.8			
				$T_J = 125^\circ\text{C}$		1.10			

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.
6. Switching characteristics are independent of operating junction temperatures.

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ELECTRICAL CHARACTERISTICS ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS							
Reverse Recovery Time	Q1	t_{RR}	$V_{GS} = 0 \text{ V}, dI_S/dt = 100 \text{ A}/\mu\text{s}, I_S = 30 \text{ A}$		29.1		ns
	Q2				40.2		
Charge Time	Q1	t_a	$V_{GS} = 0 \text{ V}, dI_S/dt = 100 \text{ A}/\mu\text{s}, I_S = 30 \text{ A}$		14.2		ns
	Q2				19.5		
Discharge Time	Q1	t_b	$V_{GS} = 0 \text{ V}, dI_S/dt = 100 \text{ A}/\mu\text{s}, I_S = 30 \text{ A}$		14.6		nC
	Q2				20.6		
Reverse Recovery Charge	Q1	Q_{RR}	$V_{GS} = 0 \text{ V}, dI_S/dt = 100 \text{ A}/\mu\text{s}, I_S = 30 \text{ A}$		21		nC
	Q2				39		

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulse Test: pulse width $\leq 300 \mu\text{s}$, duty cycle $\leq 2\%$.

6. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS – Q1

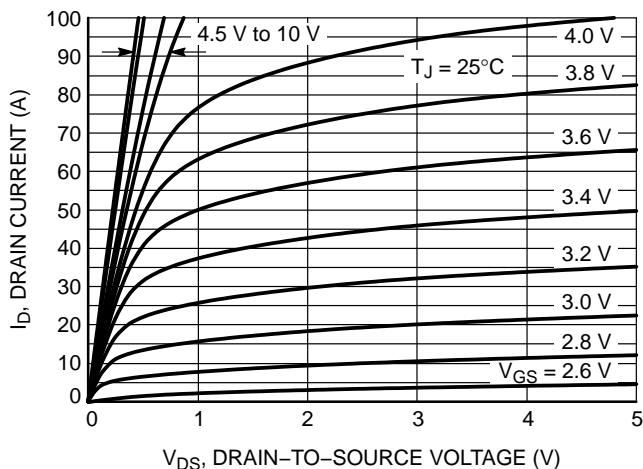


Figure 3. On-Region Characteristics

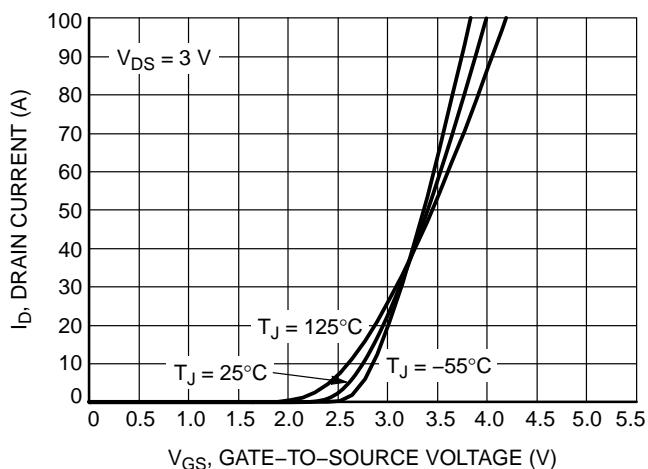


Figure 4. Transfer Characteristics

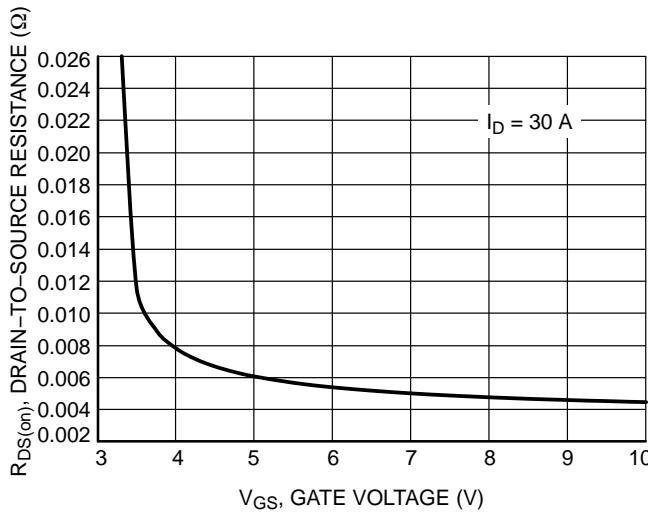


Figure 5. On-Resistance vs. Gate-to-Source Voltage

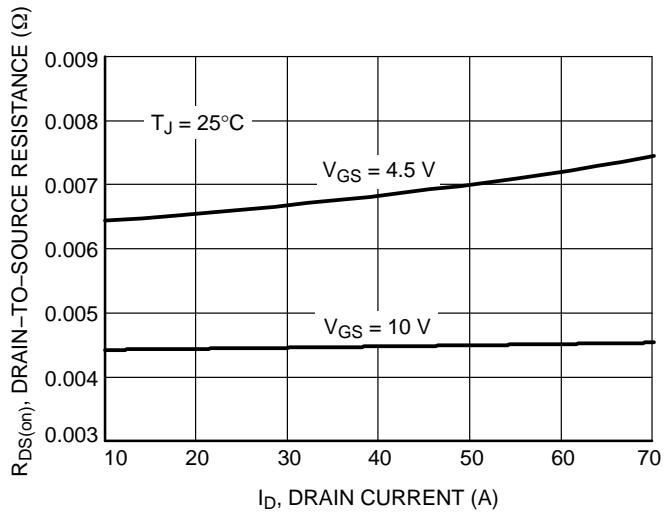


Figure 6. On-Resistance vs. Drain Current and Gate Voltage

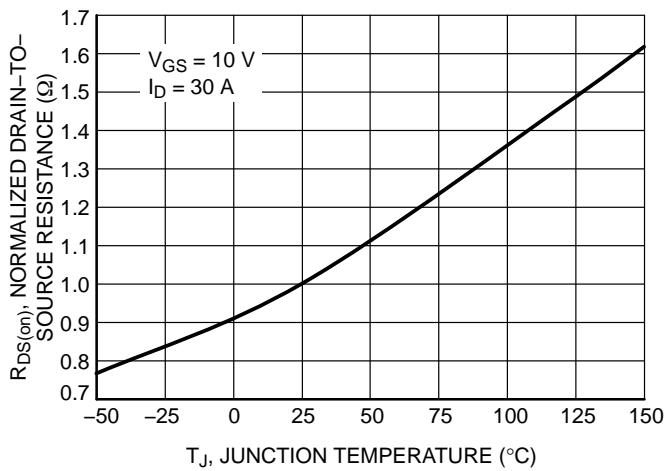


Figure 7. On-Resistance Variation with Temperature

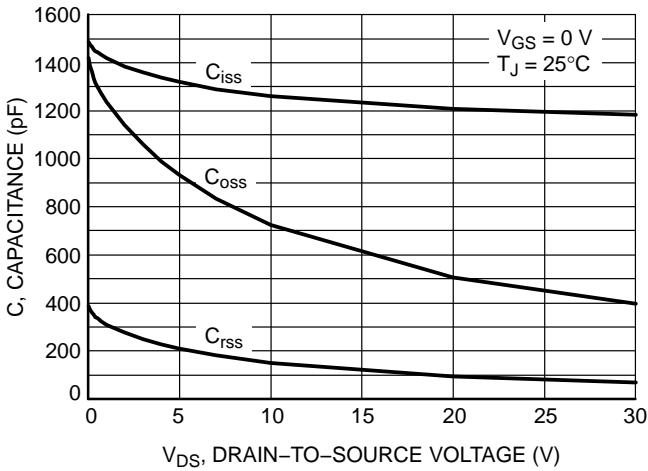


Figure 8. Capacitance Variation

TYPICAL CHARACTERISTICS – Q1

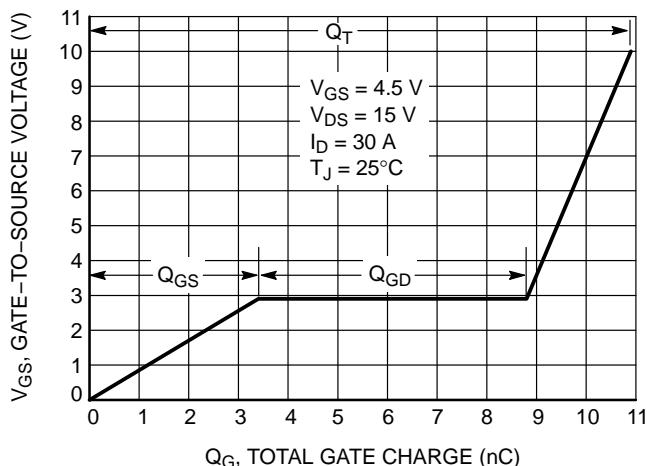


Figure 9. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

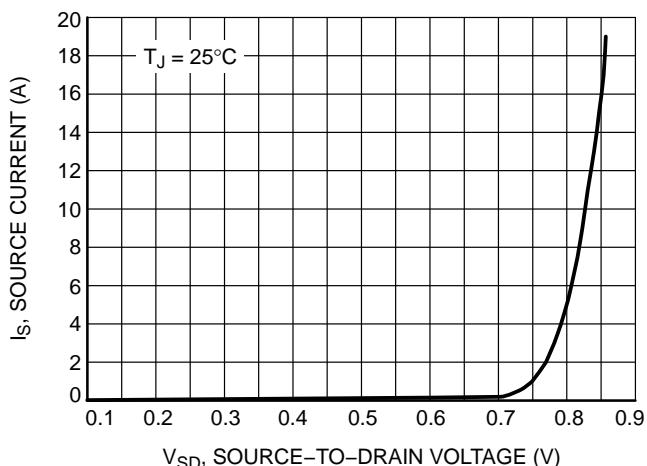


Figure 10. Diode Forward Voltage vs. Current

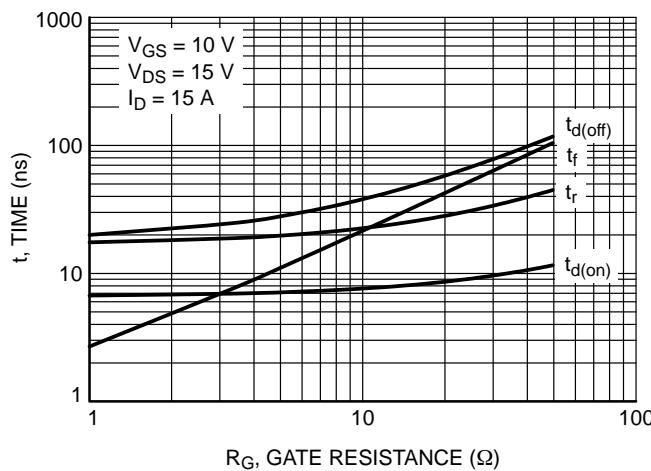


Figure 11. Resistive Switching Time Variation vs. Gate Resistance

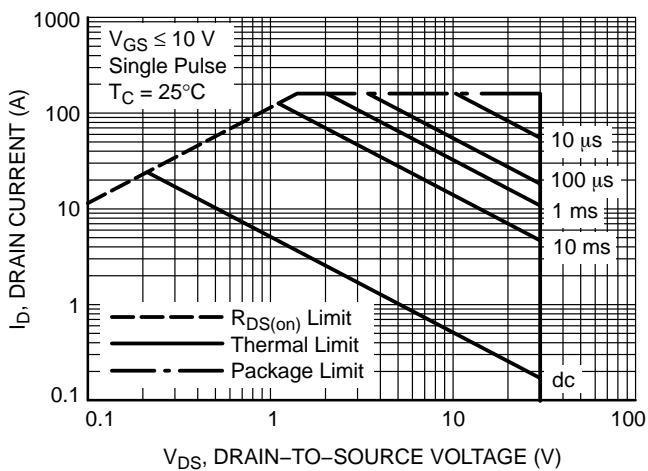


Figure 12. Maximum Rated Forward Biased Safe Operating Area

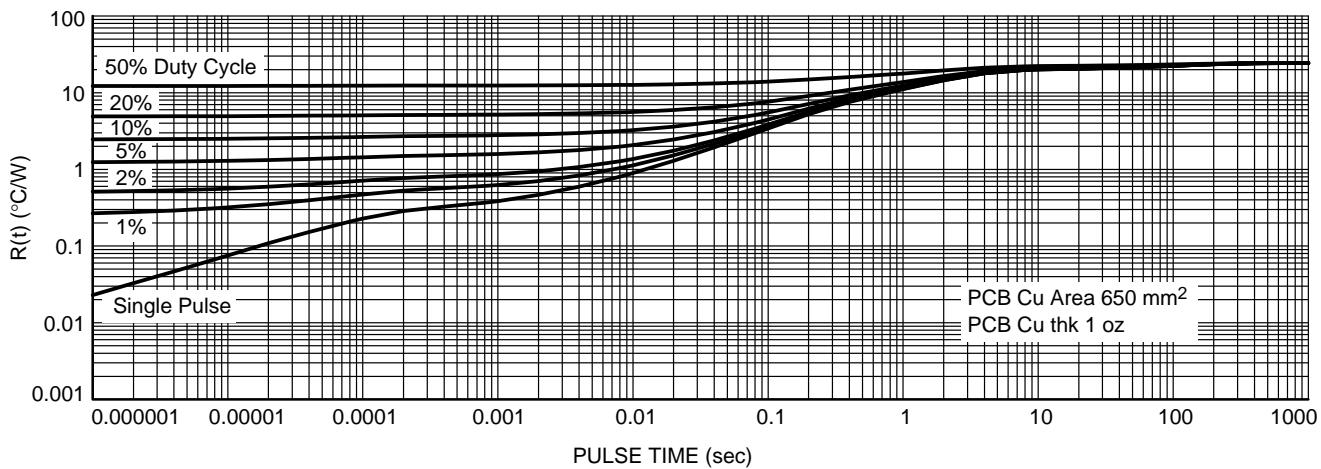


Figure 13. Thermal Characteristics

TYPICAL CHARACTERISTICS – Q2

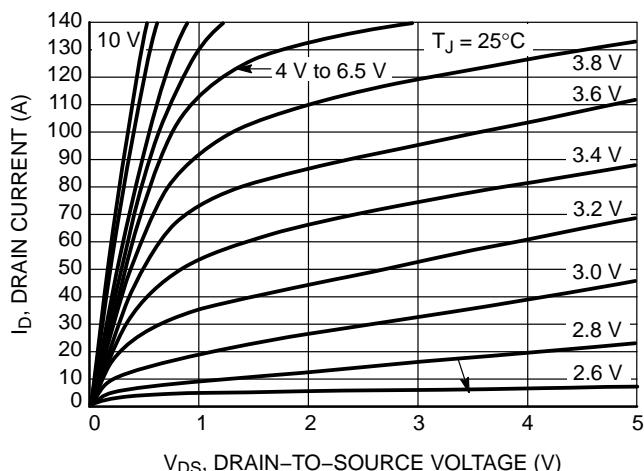


Figure 14. On-Region Characteristics

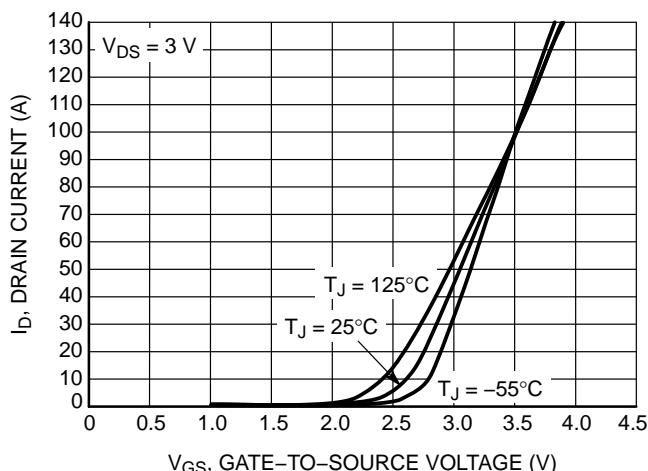


Figure 15. Transfer Characteristics

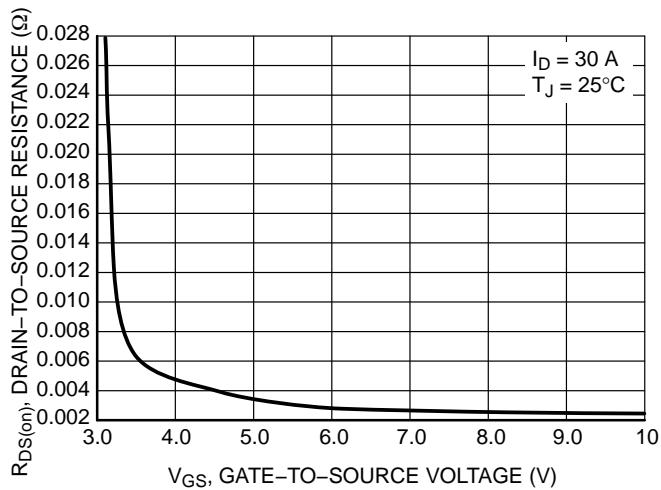


Figure 16. On-Resistance vs. V_{GS}

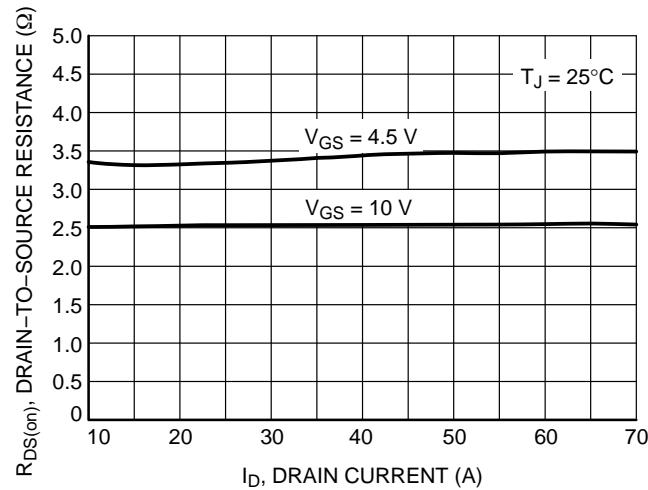


Figure 17. On-Resistance vs. Drain Current and Gate Voltage

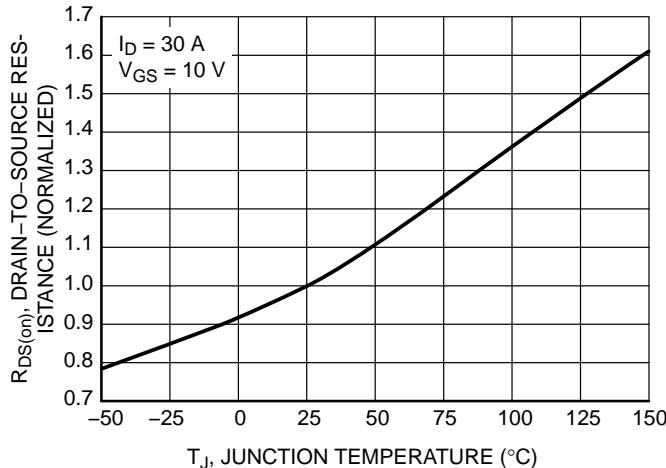


Figure 18. On-Resistance Variation with Temperature

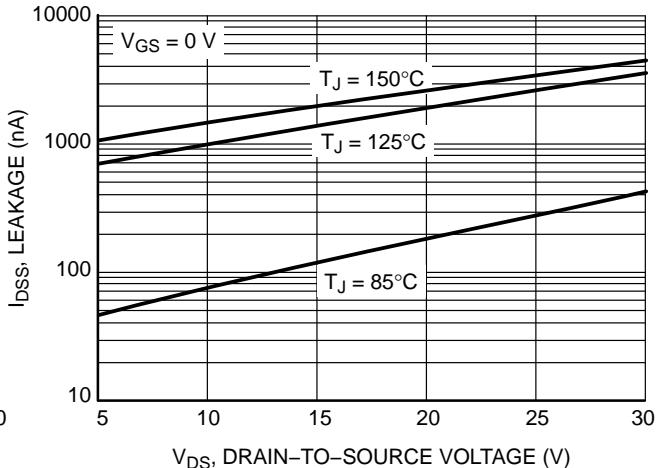


Figure 19. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS – Q2

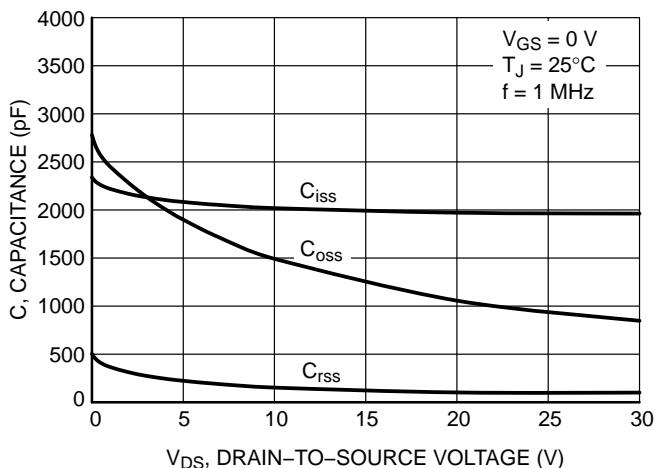


Figure 20. Capacitance Variation

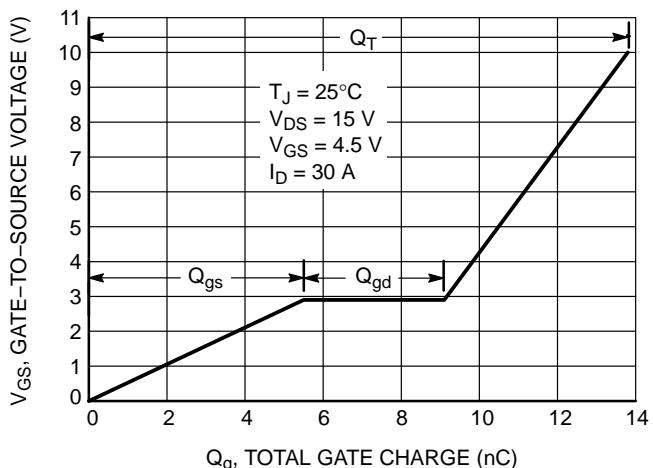


Figure 21. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

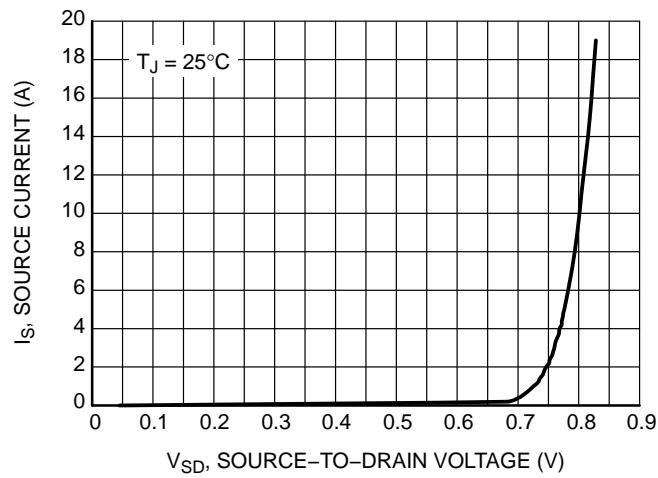
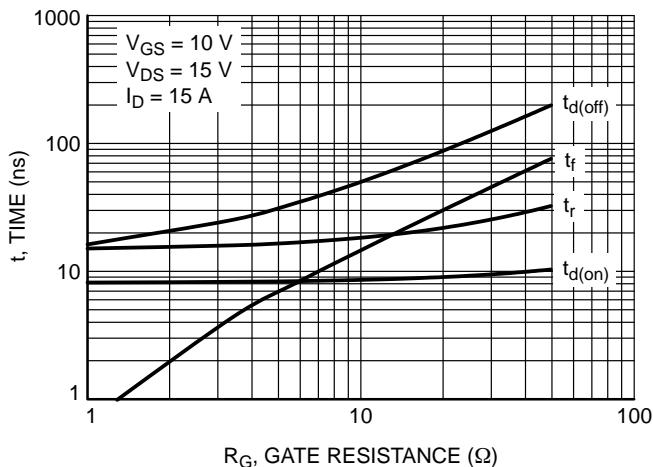
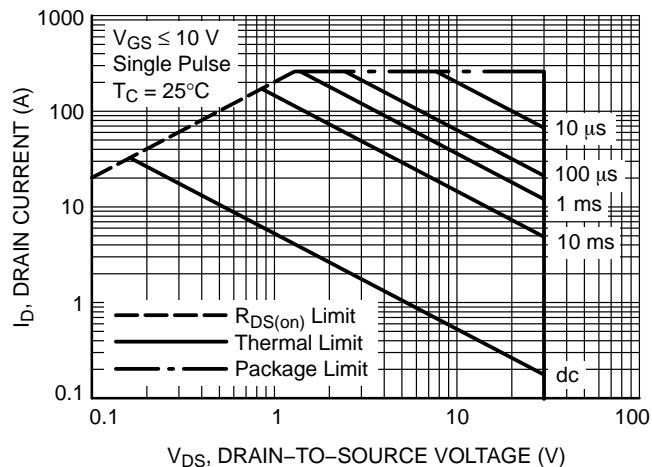
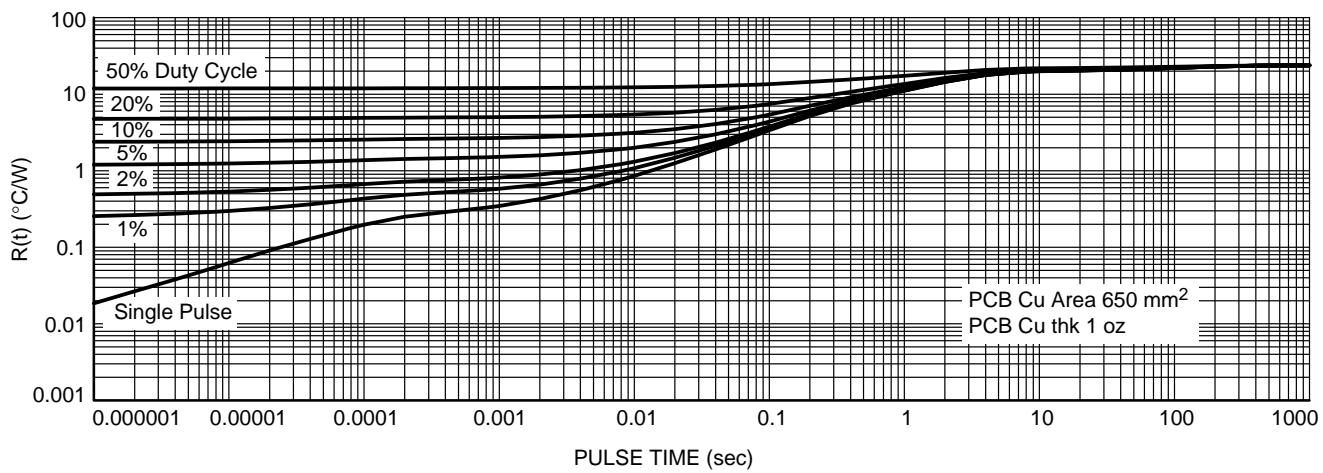


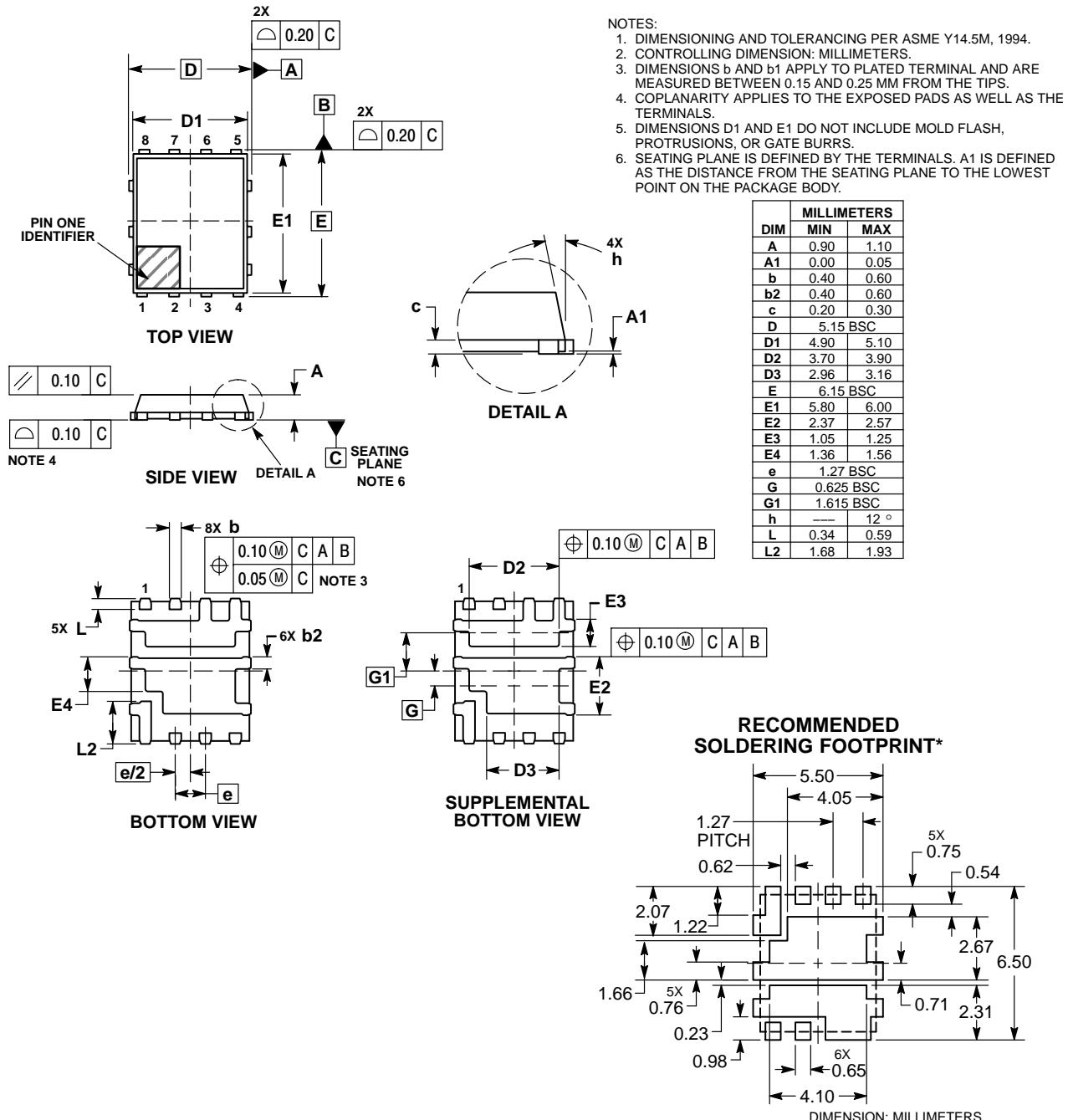
Figure 22. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS – Q2

Figure 23. Resistive Switching Time Variation vs. Gate Resistance

Figure 24. Maximum Rated Forward Biased Safe Operating Area

Figure 25. Thermal Characteristics
ORDERING INFORMATION

Device	Package	Shipping [†]
NTMFD4C87NT1G	DFN8 (Pb-Free)	1500 / Tape & Reel
NTMFD4C87NT3G	DFN8 (Pb-Free)	5000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

DFN8 5x6, 1.27P PowerPhase FET
CASE 506CR
ISSUE C

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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